International
IOR Rectifier

IRG8P25N120KDPbF
IRG8P25N120KD-EPbF

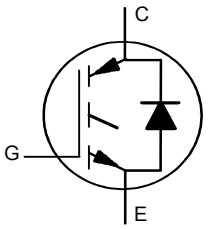
Insulated Gate Bipolar Transistor with Ultrafast Soft Recovery Diode

V_{CES} = 1200V

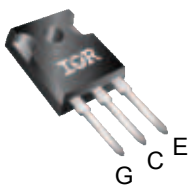
I_C = 25A, T_C =100°C

$t_{SC} \geq$ 10µs, $T_{J(max)}$ = 150°C

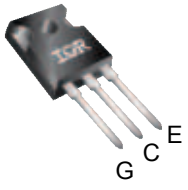
$V_{CE(ON)}$ typ. = 1.7V @ I_C = 15A



n-channel



IRG8P25N120KDPbF
TO-247AC



IRG8P25N120KD-EPbF
TO-247AD

G	C	E
Gate	Collector	Emitter

Applications

- Industrial Motor Drive
- UPS
- Solar Inverters
- Welding

Features →	Benefits
Benchmark Low $V_{CE(ON)}$	High Efficiency in a Motor Drive Applications
10µs Short Circuit SOA	Increases margin for short circuit protection scheme
Positive $V_{CE(ON)}$ Temperature Coefficient	Excellent Current Sharing in Parallel Operation
Square RBSOA and high I_{LM} rating	Rugged Transient Performance
Lead-Free, RoHS compliant	Environmentally friendly

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRG8P25N120KDPbF	TO-247AC	Tube	25	IRG8P25N120KDPbF
IRG8P25N120KD-EPbF	TO-247AD	Tube	25	IRG8P25N120KD-EPbF

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
I_C @ T_C = 25°C	Continuous Collector Current (Silicon Limited)	40	A
I_C @ T_C = 100°C	Continuous Collector Current	25	
I_{CM}	Pulse Collector Current (see fig. 2)	45	
I_{LM}	Clamped Inductive Load Current (see fig. 3)①	60	
I_F @ T_C = 25°C	Diode Continuous Forward Current	25	
I_F @ T_C = 100°C	Diode Continuous Forward Current	12	
I_{FM}	Diode Maximum Forward Current ⑤	60	
V_{GE}	Continuous Gate-to-Emitter Voltage	±30	V
P_D @ T_C = 25°C	Maximum Power Dissipation	180	W
P_D @ T_C = 100°C	Maximum Power Dissipation	70	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-40 to +150	C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw	10 lbf·in (1.1 N·m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance Junction-to-Case-(each IGBT) ②	—	—	0.7	°C/W
$R_{\theta JC}$ (Diode)	Thermal Resistance Junction-to-Case-(each Diode) ②	—	—	1.5	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink (flat, greased surface)	—	0.24	—	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (typical socket mount)	—	40	—	

 © 2014 International Rectifier

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	V_{GE} = 0V, I_C = 250µA ③
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.92	—	V/°C	V_{GE} = 0V, I_C = 1mA (25°C-150°C)
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.7	2.0	V	I_C = 15A, V_{GE} = 15V, T_J = 25°C
		—	2.0	—		I_C = 15A, V_{GE} = 15V, T_J = 150°C
$V_{GE(th)}$	Gate Threshold Voltage	5.0	—	6.5	V	V_{CE} = V_{GE}, I_C = 600µA
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage Temperature Coeff.	—	-16	—	mV/°C	V_{CE} = V_{GE}, I_C = 600µA (25°C-150°C)
gfe	Forward Transconductance	—	8.5	—	S	V_{CE} = 50V, I_C = 15A, PW = 20µs
I_{CES}	Collector-to-Emitter Leakage Current	—	1	30	µA	V_{GE} = 0V, V_{CE} = 1200V
		—	1	—	mA	V_{GE} = 0V, V_{CE} = 1200V, T_J = 150°C
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±30V
V_F	Diode Forward Voltage Drop	—	2.1	2.7	V	I_F = 15A
		—	2.4	—		I_F = 15A, T_J = 150°C

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max④	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	90	135	nC	I_C = 15A
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	5.0	—		V_{GE} = 15V
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	60	—		V_{CC} = 600V
E_{on}	Turn-On Switching Loss	—	0.8	—	mJ	I_C = 15A, V_{CC} = 600V, V_{GE}=15V R_G = 10Ω, T_J = 25°C Energy losses include tail & diode reverse recovery ⑥
E_{off}	Turn-Off Switching Loss	—	0.9	—		
E_{total}	Total Switching Loss	—	1.7	—		
$t_{d(on)}$	Turn-On delay time	—	20	—	ns	
t_r	Rise time	—	20	—		
$t_{d(off)}$	Turn-Off delay time	—	170	—		
t_f	Fall time	—	190	—		
E_{on}	Turn-On Switching Loss	—	1.3	—	mJ	I_C = 15A, V_{CC} = 600V, V_{GE}=15V R_G = 10Ω, T_J = 150°C Energy losses include tail & diode reverse recovery ⑥
E_{off}	Turn-Off Switching Loss	—	1.7	—		
E_{total}	Total Switching Loss	—	3.0	—		
$t_{d(on)}$	Turn-On delay time	—	20	—	ns	
t_r	Rise time	—	20	—		
$t_{d(off)}$	Turn-Off delay time	—	260	—		
t_f	Fall time	—	325	—		
C_{ies}	Input Capacitance	—	1800	—	pF	V_{GE} = 0V
C_{oes}	Output Capacitance	—	90	—		V_{CC} = 30V
C_{res}	Reverse Transfer Capacitance	—	45	—		f = 1.0Mhz
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T_J = 150°C, I_C = 60A V_{CC} = 960V, Vp ≤ 1200V V_{GE} = +20V to 0V
SCSOA	Short Circuit Safe Operating Area	10	—	—	µs	T_J = 150°C,V_{CC} = 600V, Vp ≤ 1200V V_{GE} = +15V to 0V
Erec	Reverse Recovery Energy of the Diode	—	0.7	—	mJ	T_J = 150°C
t_{rr}	Diode Reverse Recovery Time	—	70	—	ns	V_{CC} = 600V, I_F = 15A
I_{rr}	Peak Reverse Recovery Current	—	29	—	A	V_{GE} = 15V, Rg = 10Ω

Notes:

① V_{CC} = 80% (V_{CES}), V_{GE} = 20V.

② R_θ is measured at T_J of approximately 90°C.

③ Refer to AN-1086 for guidelines for measuring $V_{(BR)CES}$ safely.

④ Maximum limits are based on statistical sample size characterization.

⑤ Pulse width limited by max. junction temperature.

⑥ Values influenced by parasitic L and C in measurement.

 © 2014 International Rectifier

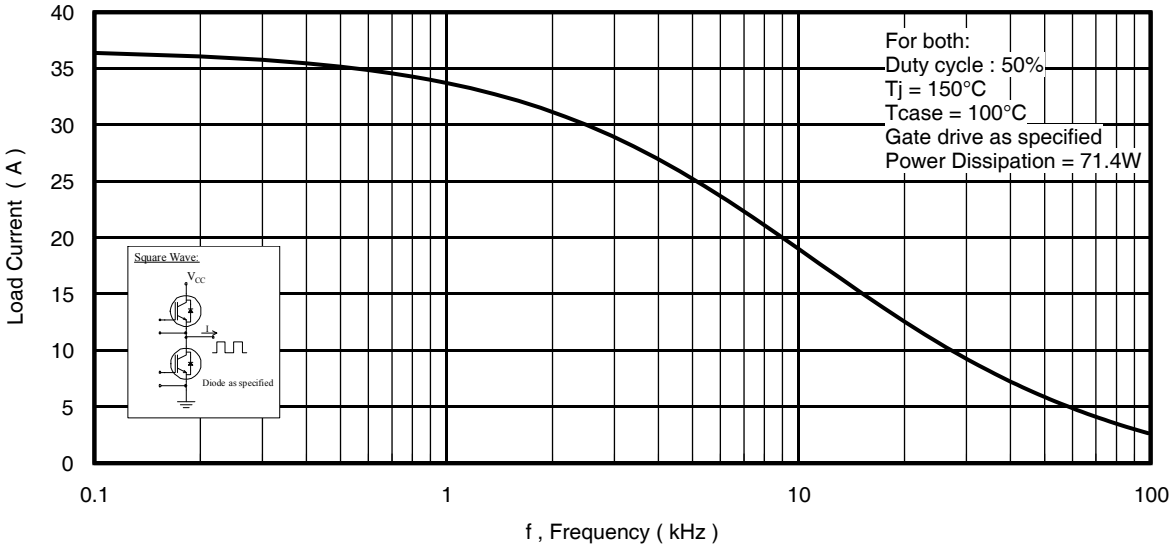


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

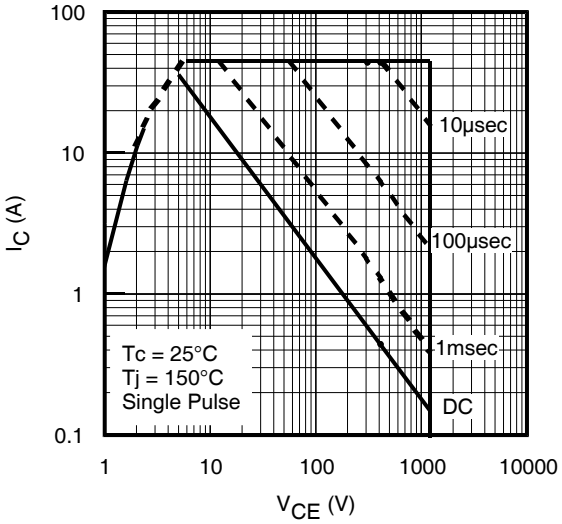


Fig. 2 - Forward SOA
T_C = 25°C; T_J ≤ 150°C; V_{GE} = 15V

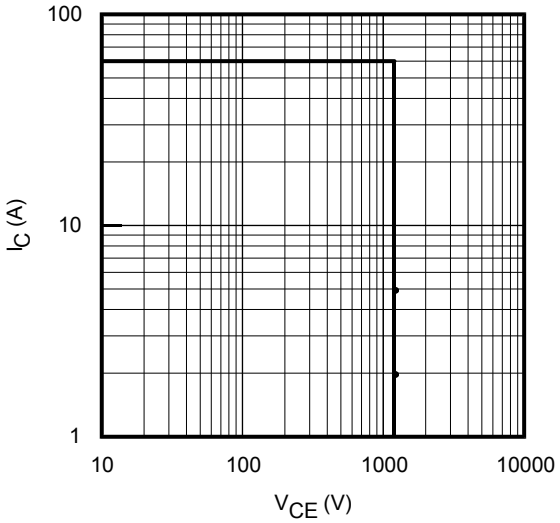


Fig. 3 - Reverse Bias SOA
T_J = 150°C; V_{GE} = 20V

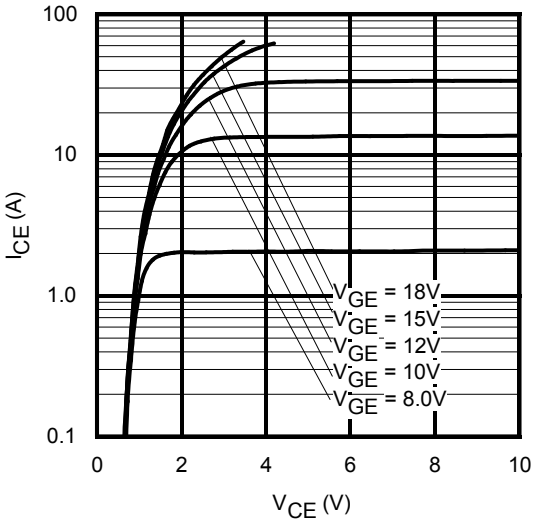


Fig. 4 - Typ. IGBT Output Characteristics
T_J = 25°C; tp = 20µs

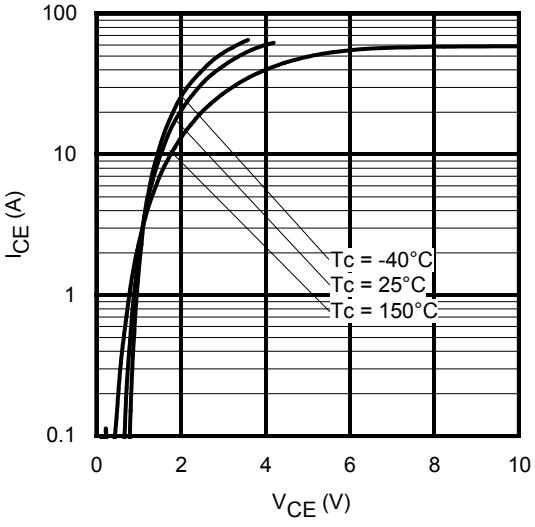


Fig. 5 - Typ. IGBT Saturation Voltage
V_{GE} = 15V; tp = 20µs

 © 2014 International Rectifier

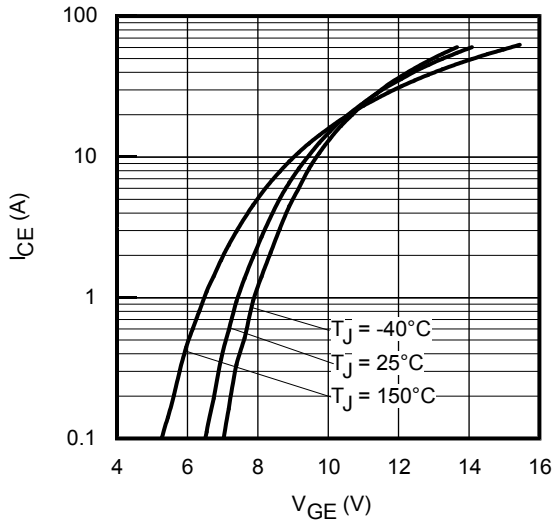


Fig. 6 - Typ. Transfer Characteristics
V_{CE} = 50V; tp = 20µs

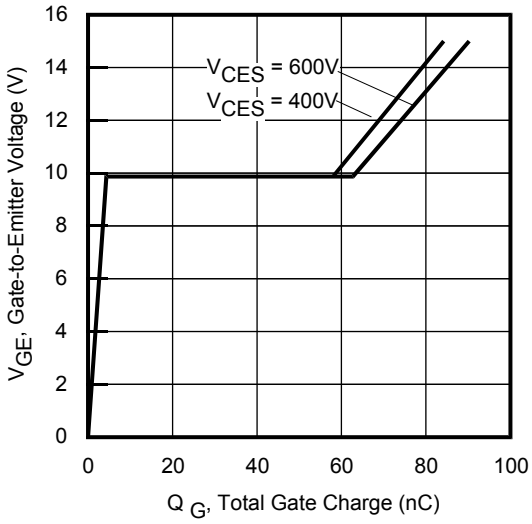


Fig. 7 - Typical Gate Charge vs. V_{GE}
I_{CE} = 15A

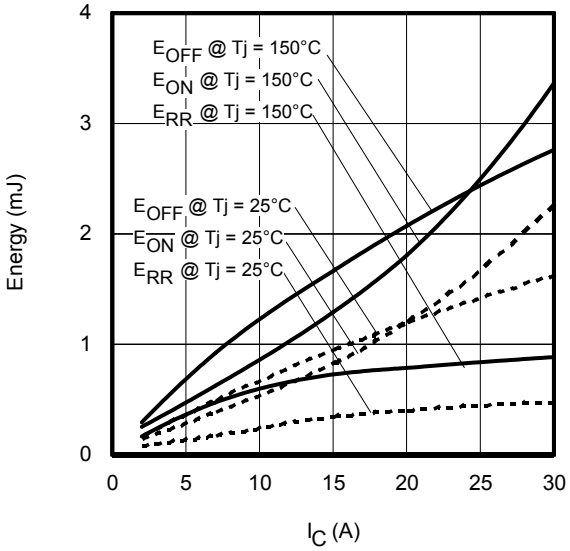


Fig. 8 - Typ. Energy Loss vs. I_C
V_{CE} = 600V, R_G = 10Ω; V_{GE} = 15V

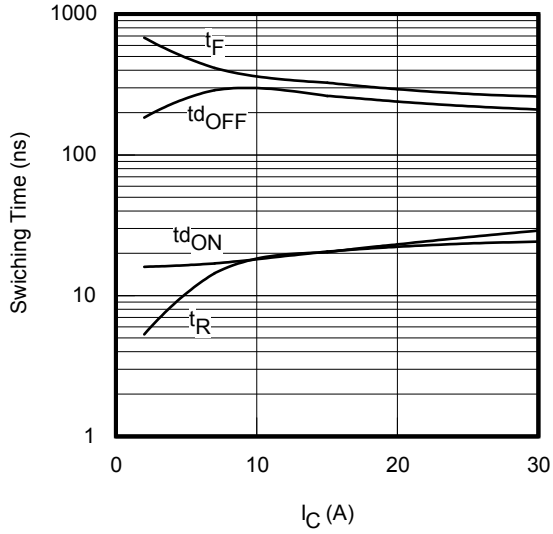


Fig. 9 - Typ. Switching Time vs. I_C
T_J = 150°C; V_{CE} = 600V, R_G = 10Ω; V_{GE} = 15V

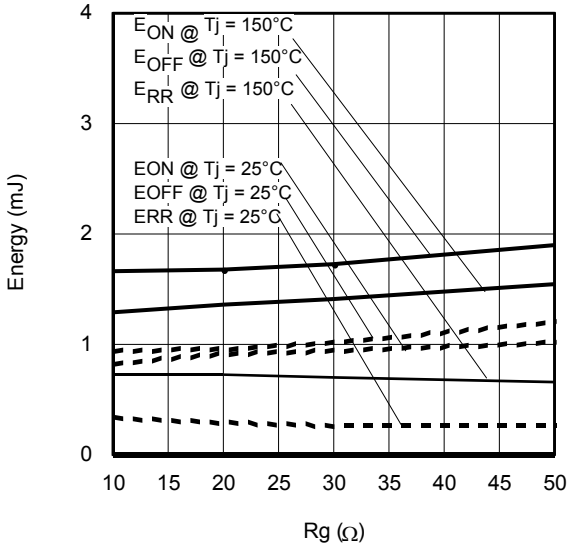


Fig. 10 - Typ. Energy Loss vs. R_G
V_{CE} = 600V, I_{CE} = 15A; V_{GE} = 15V

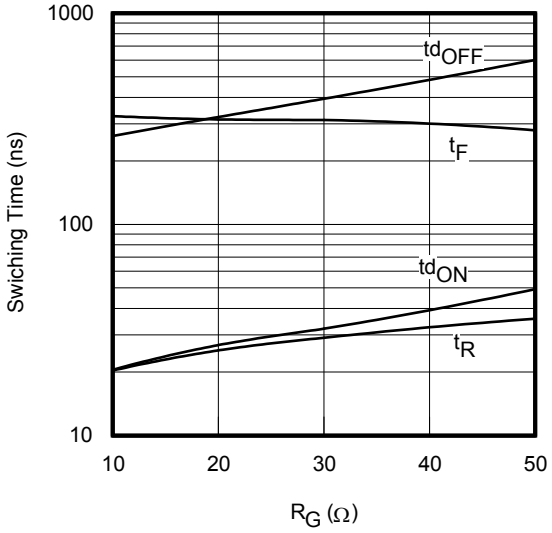


Fig. 11 - Typ. Switching Time vs. R_G
T_J = 150°C; V_{CE} = 600V, I_{CE} = 15A; V_{GE} = 15V

 © 2014 International Rectifier

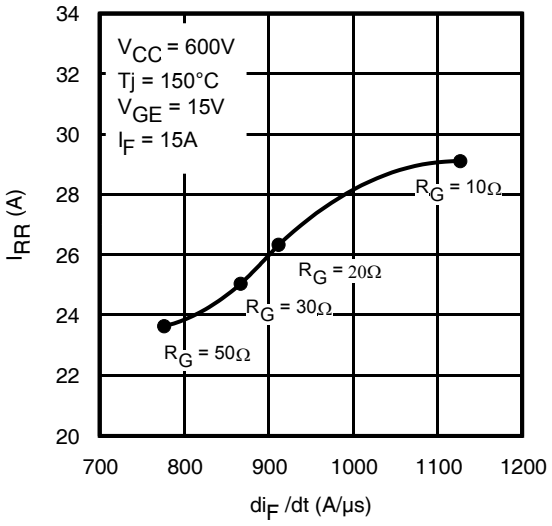


Fig. 12 - Typ. I_{RR} vs. di/dt

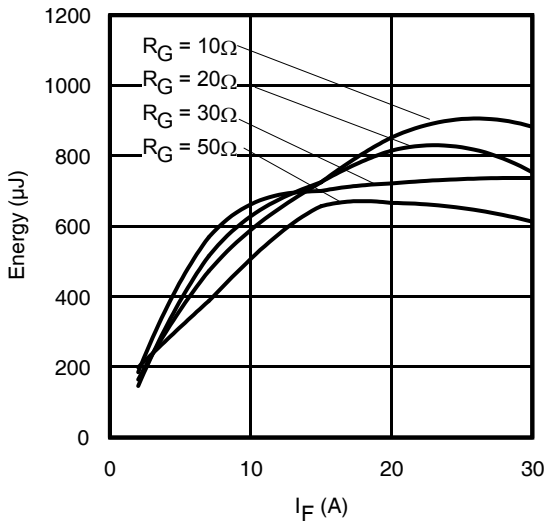


Fig. 13 - Typ. Diode E_{RR} vs. I_F
T_J = 150°C

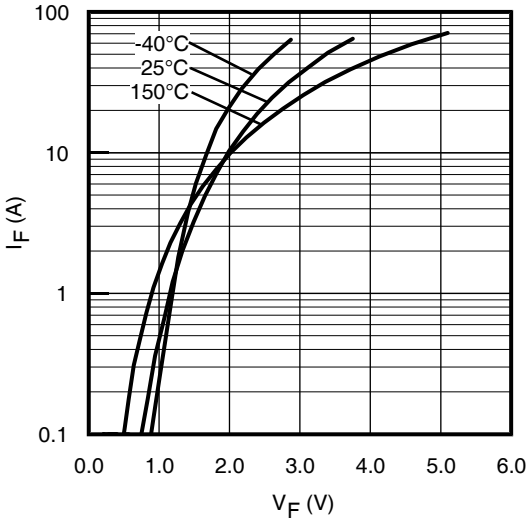


Fig. 14 - Typ. Diode Forward
Voltage Drop Characteristics

 © 2014 International Rectifier

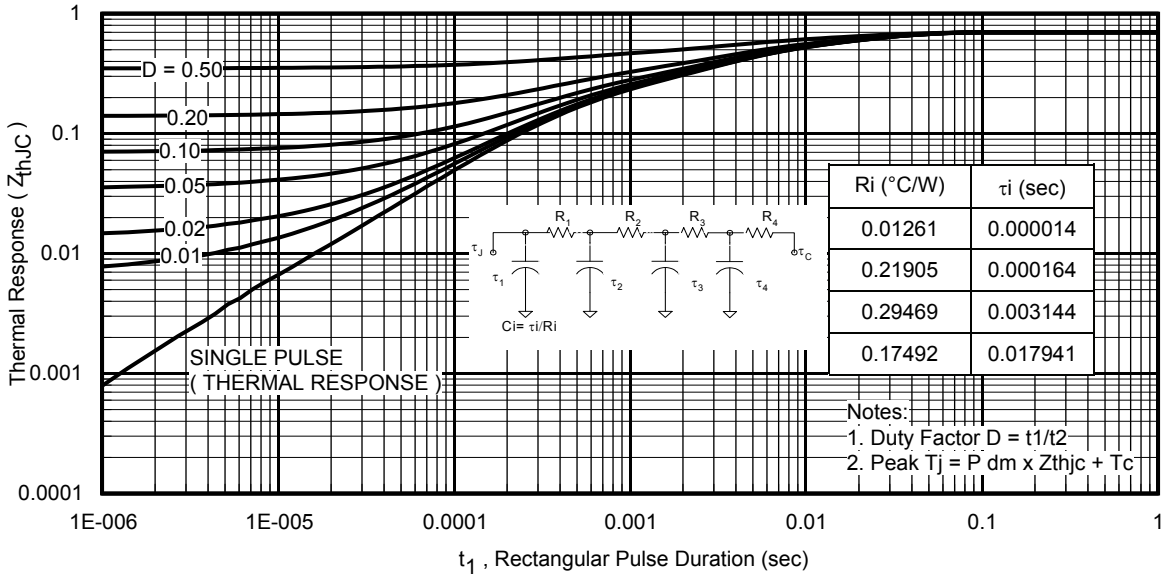


Fig. 15 - Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

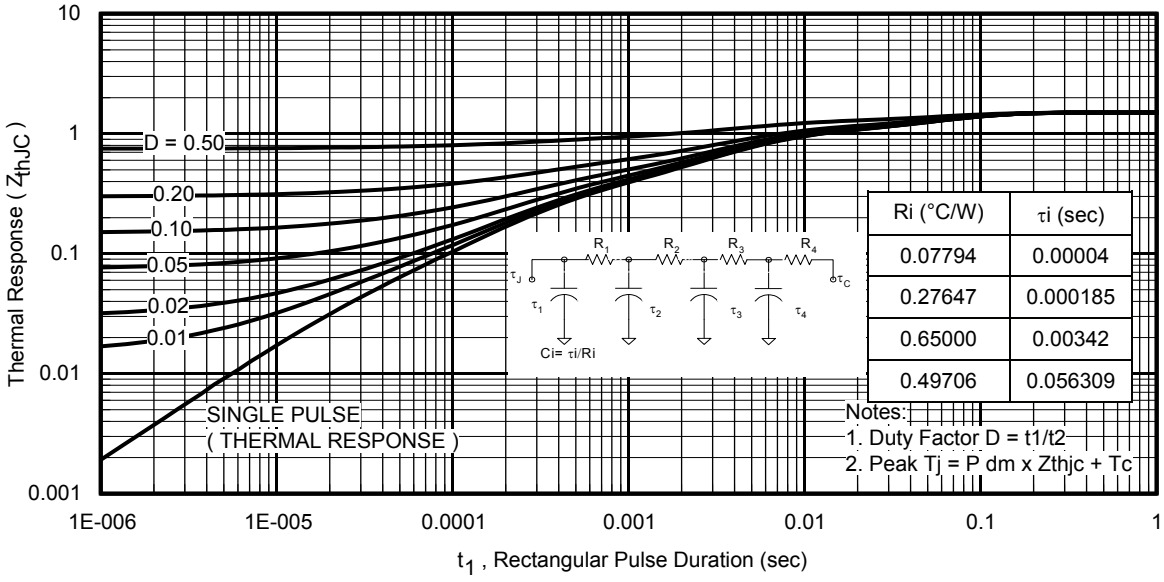


Fig. 16 - Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)

 © 2014 International Rectifier

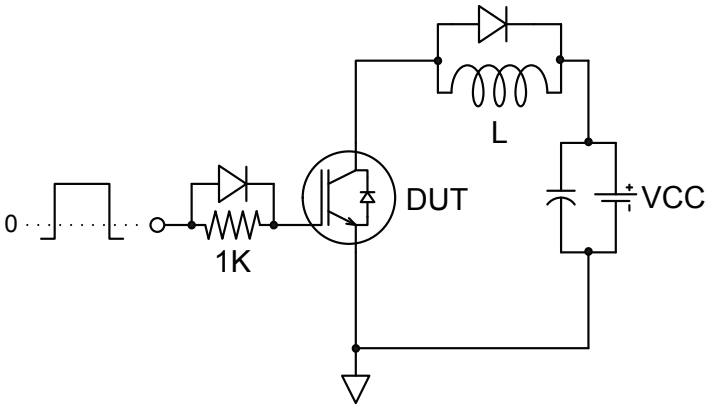


Fig.C.T.1 - Gate Charge Circuit (turn-off)

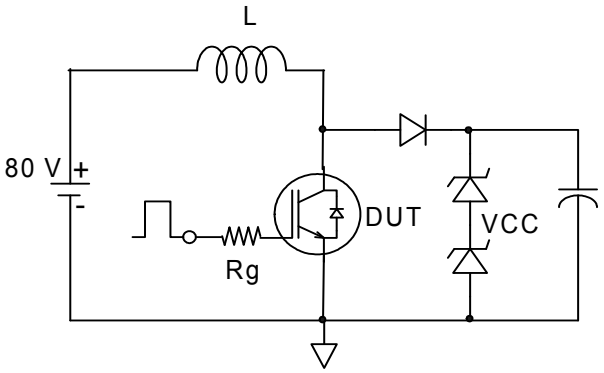


Fig.C.T.2 - RBSOA Circuit

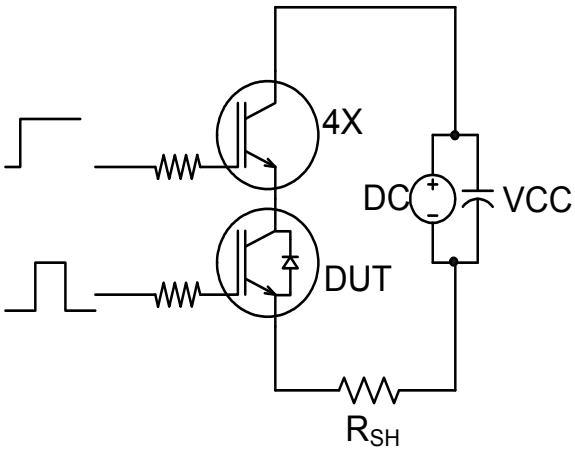


Fig.C.T.3 - S.C. SOA Circuit

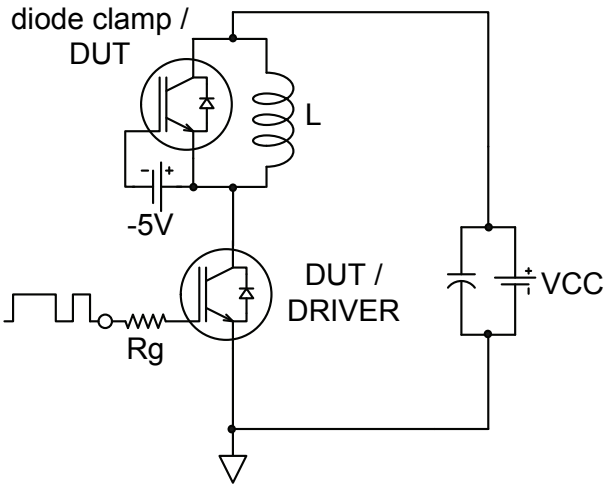


Fig.C.T.4 - Switching Loss Circuit
(Board Stray Inductance 180nH)

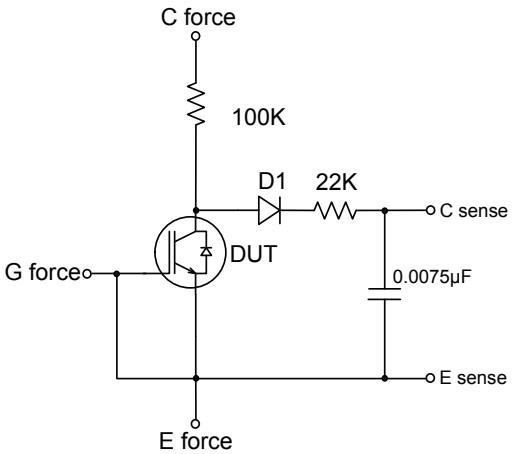


Fig.C.T.5 - BVCES Filter Circuit

 © 2014 International Rectifier

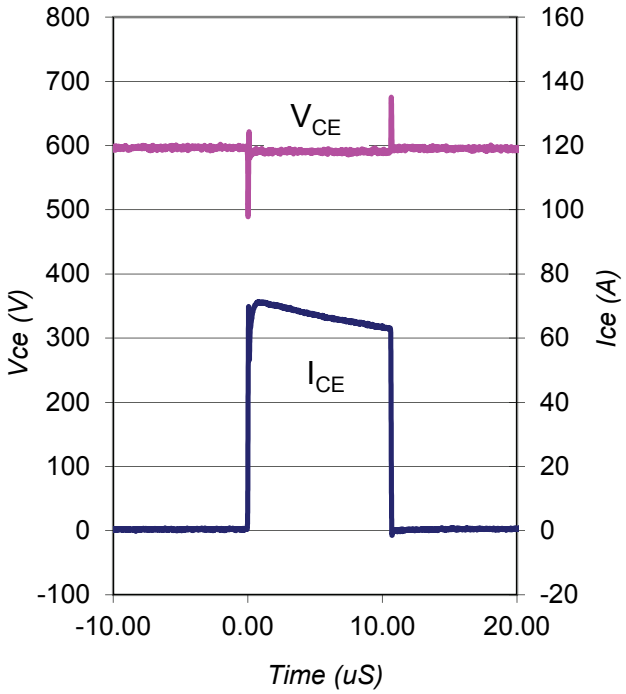
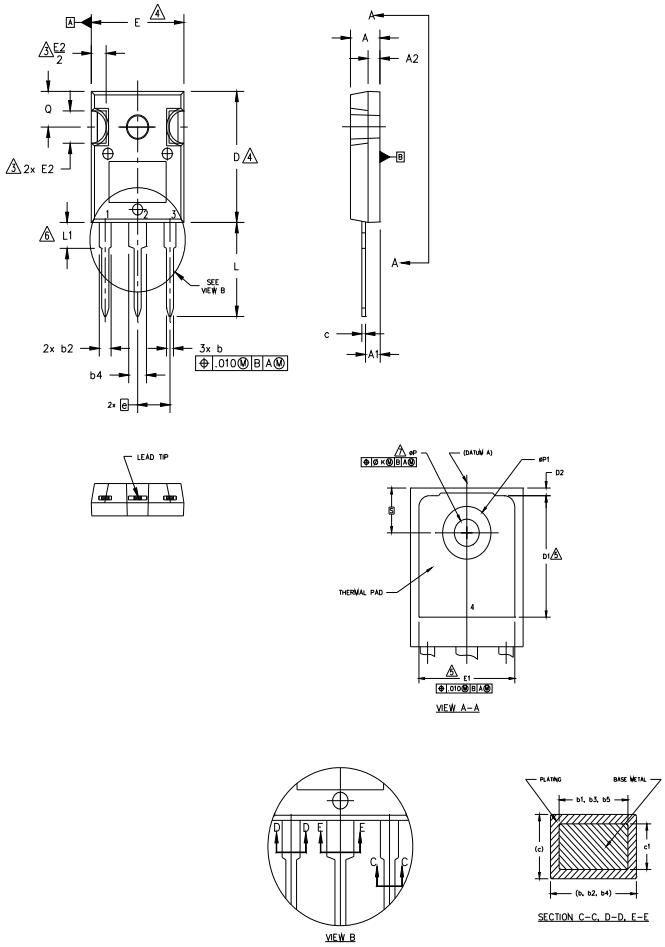


Fig. WF1 - Typ. S.C. Waveform
@ T_J = 150°C using Fig. CT.3

 © 2014 International Rectifier

TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. øP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC .

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	–	13.08	–	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	–	13.46	–	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
øk	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
øP	.140	.144	3.56	3.66	
øP1	–	.291	–	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

1.– GATE
2.– DRAIN
3.– SOURCE
4.– DRAIN

IGBTs, CoPACK

1.– GATE
2.– COLLECTOR
3.– EMITTER
4.– COLLECTOR

DIODES

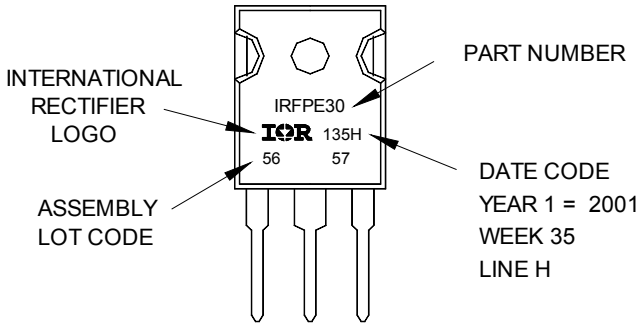
1.– ANODE/OPEN
2.– CATHODE
3.– ANODE

TO-247AC Part Marking Information

Notes: This part marking information applies to devices produced after 02/26/2001

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2001
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position
indicates "Lead-Free"



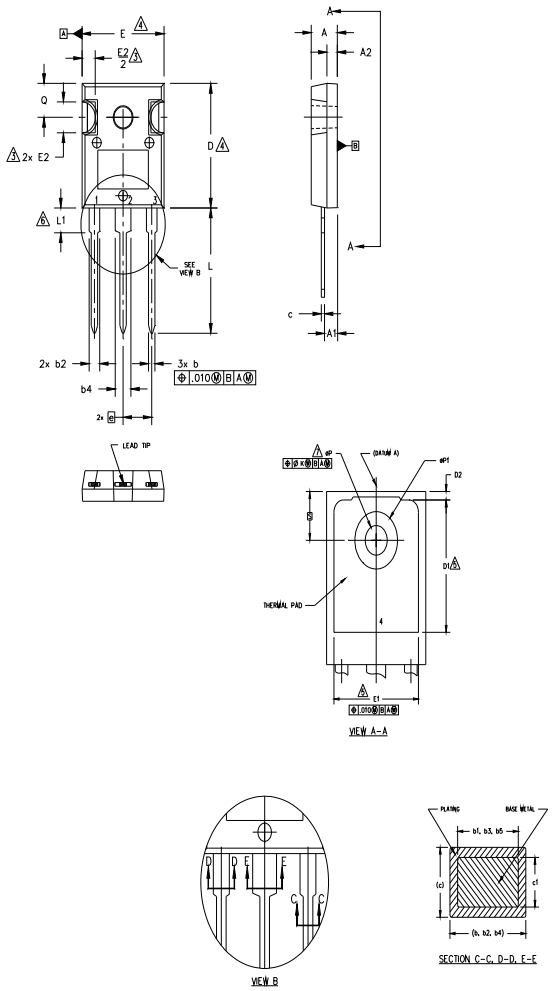
TO-247AC package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

 © 2014 International Rectifier

TO-247AD Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. øP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AD.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	–	13.08	–	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	–	13.46	–	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
øk	.010		0.25		
L	.780	.827	19.57	21.00	
L1	.146	.169	3.71	4.29	
øP	.140	.144	3.56	3.66	
øP1	–	.291	–	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

1.– GATE
2.– DRAIN
3.– SOURCE
4.– DRAIN

IGBTs, CoPACK

1.– GATE
2.– COLLECTOR
3.– EMITTER
4.– COLLECTOR

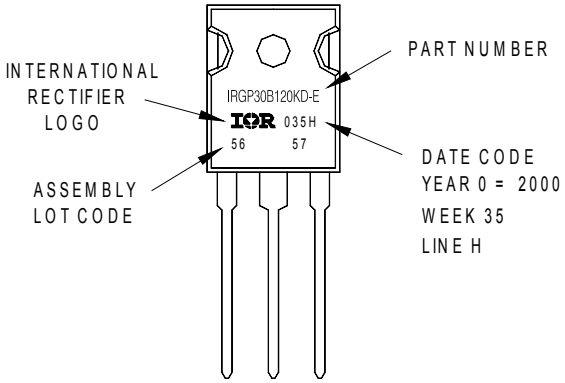
DIODES

1.– ANODE/OPEN
2.– CATHODE
3.– ANODE

TO-247AD Part Marking Information

EXAMPLE: THIS IS AN IRGP30B120KD-E
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position indicates "Lead-Free"



TO-247AD package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

 © 2014 International Rectifier

Qualification Information†

Qualification Level	Industrial† (per JEDEC JESD47F) ††	
Moisture Sensitivity Level	TO-247AC	N/A
	TO-247AD	N/A
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: http://www.irf.com/product-info/reliability/

†† Applicable version of JEDEC standard at the time of product release.

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA
To contact International Rectifier, please visit http://www.irf.com/whoto-call/

 © 2014 International Rectifier